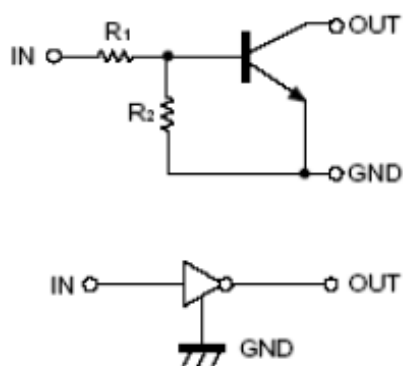


DIGITAL TRANSISTOR (NPN)

FEATURES

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- Only the on/off conditions need to be set for operation, making device design easy.



Digital Transistor (built-in resistor)

DTC124EM

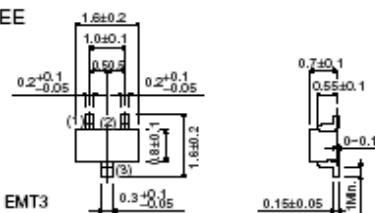


ROHM : VMT3

(1) IN
(2) GND
(3) OUT

Abbreviated symbol : 25

DTC124EE

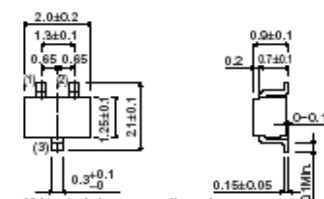


ROHM : EMT3

(1) GND
(2) IN
(3) OUT

Abbreviated symbol : 25

DTC124EUA



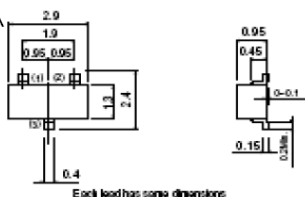
ROHM : UMT3

All terminals have same dimensions

(1) GND
(2) IN
(3) OUT

Abbreviated symbol : 25

DTC124ECA



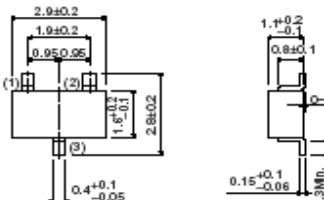
Each load has some dimensions

(1) GND
(2) IN
(3) OUT

EIAJ:SST3

Abbreviated symbol : 26

DTC124EKA



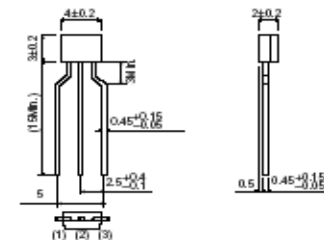
ROHM : SMT3
EIAJ : SC-59

All terminals have same dimensions

(1) GND
(2) IN
(3) OUT

Abbreviated symbol : 25

DTC124ESA



ROHM : SPT
EIAJ : SC-72

(1) GND
(2) OUT
(3) IN

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

ABSOLUTE MAXIMUM RATINGS

Parameters	Symbols	Limits (DTC124E□)						UNITS
		M	E	UA	KA	CA	SA	
Supply Voltage	V _{CC}	50						V
Input Voltage	V _{IN}	-10~40						V
Output Current	I _O	30						mA
	I _{C(MAX)}	100						
Power Dissipation	P _d	150		200			300	mW
Junction Temperature	T _J	150						°C
Storage Temperature	T _{STG}	-55~150						°C

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Input Voltage	$V_{I(off)}$	$V_{CC}=5V, I_O=100\mu A$			0.5	V
	$V_{I(on)}$	$V_O=0.2V, I_O=5mA$	3			
Output Voltage	$V_{O(on)}$	$I_O/I_I=10mA/0.5mA$		0.1	0.3	V
Input Current	I_I	$V_I=5V$			0.36	mA
Output Current	$I_{O(off)}$	$V_{CC}=50V, V_I=0$			0.5	μA
DC Current Gain	G_I	$V_O=5V, I_O=5mA$	56			
Input Resistance	R_1		15.4	22	28.6	K Ω
Resistance Ratio	R_2/R_1		0.8	1	1.2	
Transition Frequency	f_T	$V_{CE}=10V, I_E=-5mA,$ $f=100MHz$		250		MHz